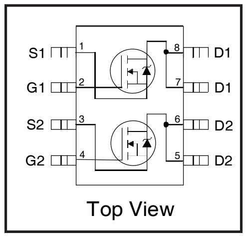
Features

HEXFET® Power MOSFET

- Advanced Planar Technology
- Dual N Channel MOSFET
- Low On-Resistance
- Logic Level Gate Drive
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Lead-Free, RoHS Compliant
- Automotive Qualified*



$V_{(BR)DSS}$	30V
$R_{DS(on)}$ max.	0.05Ω
I_D	5.3A

Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

SO-8
AUIRF7303Q

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRF7303Q	SO-8	Tube	95	AUIRF7303Q
		Tape and Reel	4000	AUIRF7303QTR

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V	5.3	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 10V	4.4	
I_{DM}	Pulsed Drain Current ①	44	
P_D @T_A = 25°C	Power Dissipation	2.4	W
	Linear Derating Factor	0.02	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②	414	mJ
$E_{AS(Tested)}$	Single Pulse Avalanche Energy⑤	1160	
dv/dt	Peak Diode Recovery dv/dt ③	1.6	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C

Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ⑥	62.5	°C/W

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*Qualification standards can be found at http://www.irf.com/

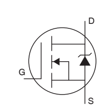
Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	——	——	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.03	——	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	——	0.05	Ω	V_{GS} = 10V, I_D = 2.7A ④
		——	——	0.08		V_{GS} = 4.5V, I_D = 2.1A ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	——	3.0	V	V_{DS} = V_{GS}, I_D = 100μA
gfs	Forward Transconductance	5.6	——	——	S	V_{DS} = 15V, I_D = 2.7A
I_{DSS}	Drain-to-Source Leakage Current	——	——	1.0	μA	V_{DS} = 24V, V_{GS} = 0V
		——	——	25		V_{DS} = 24V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	-100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	——	——	100		V_{GS} = -20V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge	——	14	21	nC	I_D = 2.7A
Q_{gs}	Gate-to-Source Charge	——	1.5	2.3		V_{DS} = 15V
Q_{gd}	Gate-to-Drain ("Miller") Charge	——	4.4	6.6		V_{GS} = 10V ④
$t_{d(on)}$	Turn-On Delay Time	——	2.9	——	ns	V_{DD} = 15V
t_r	Rise Time	——	6.2	——		I_D = 2.7A
$t_{d(off)}$	Turn-Off Delay Time	——	15	——		R_G = 6.8Ω
t_f	Fall Time	——	7.8	——		V_{GS} =10V ④
C_{iss}	Input Capacitance	——	515	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	217	——		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	——	90	——		f = 1.0MHz

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	3.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	——	——	44		
V_{SD}	Diode Forward Voltage	——	——	1.0	V	T_J = 25°C, I_S = 2.7A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	——	26	39	ns	T_J = 25°C, I_F = 2.7A
Q_{rr}	Reverse Recovery Charge	——	50	75	nC	di/dt = 100A/μs ④

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Limited by T_{Jmax}, starting T_J = 25°C, L = 118mH, R_G = 50Ω, I_{AS} = 2.7A, V_{GS} =10V. Part not recommended for use above this value.

③ $I_{SD} \leq$ 2.7A, di/dt ≤ 389A/μs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C.

④ Pulse width ≤ 400μs; duty cycle ≤ 2%.

⑤ This value determined from sample failure population, starting T_J = 25°C, L = 118mH, R_G = 50Ω, I_{AS} = 2.7A, V_{GS} =10V.

⑥ Surface mounted on FR-4 board, t ≤ 10sec..

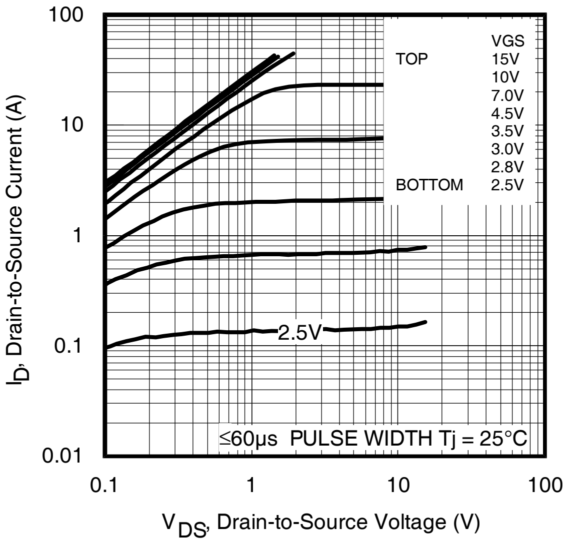


Fig 1. Typical Output Characteristics

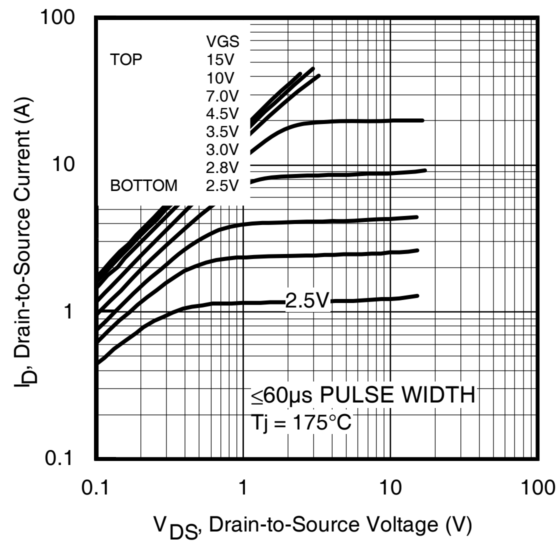


Fig 2. Typical Output Characteristics

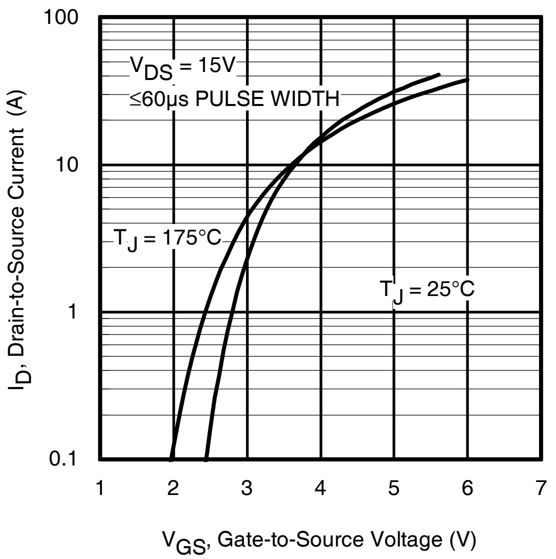


Fig 3. Typical Transfer Characteristics

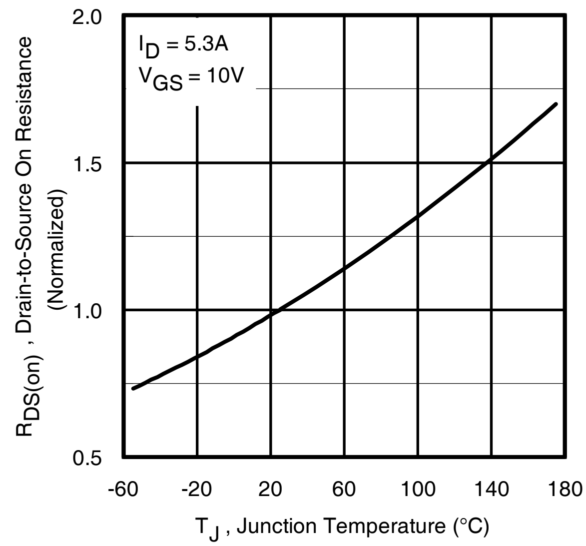


Fig 4. Normalized On-Resistance Vs. Temperature

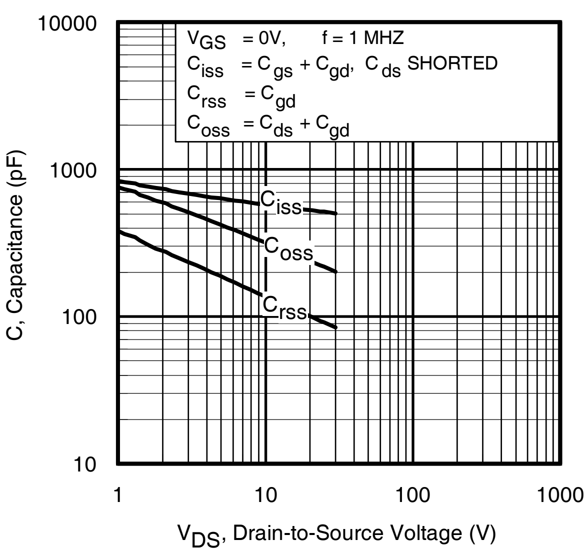


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

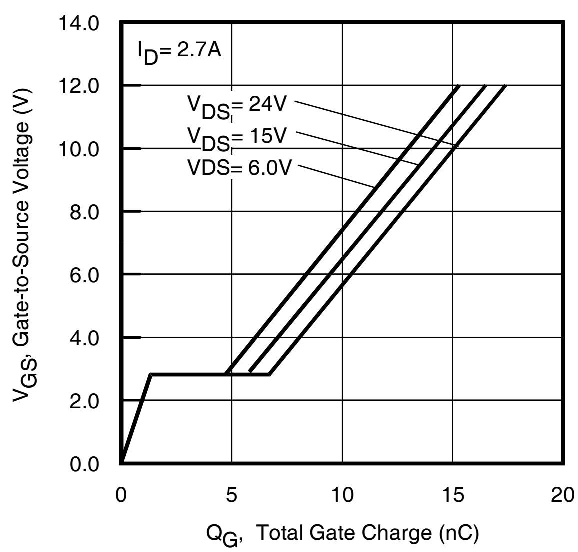


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

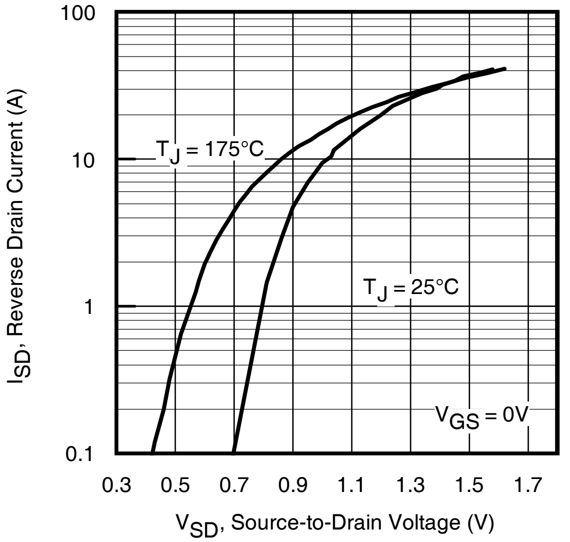


Fig 7. Typical Source-Drain Diode Forward Voltage

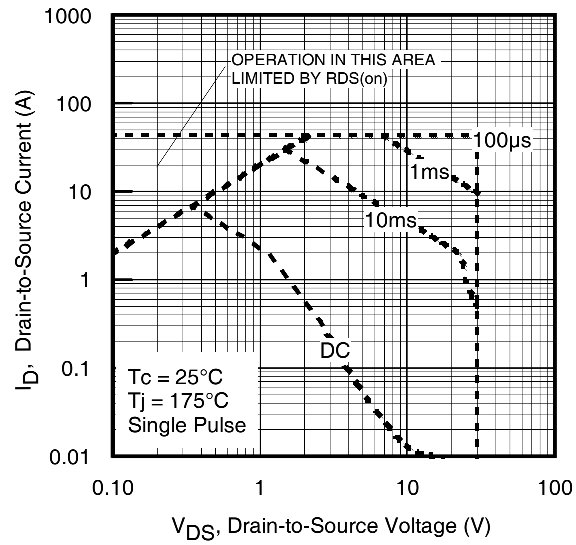


Fig 8. Maximum Safe Operating Area

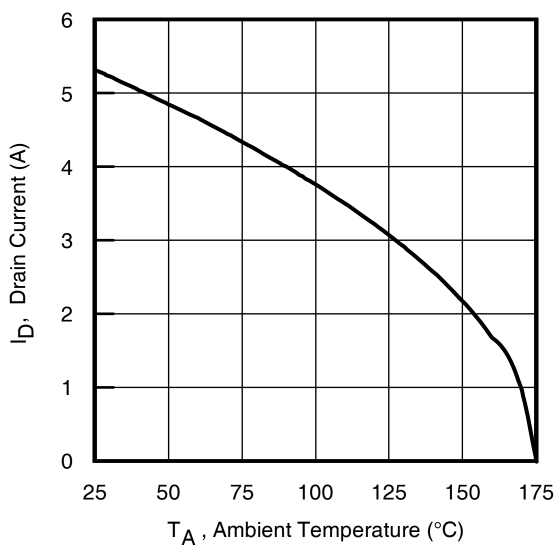


Fig 9. Maximum Drain Current Vs. Ambient Temperature

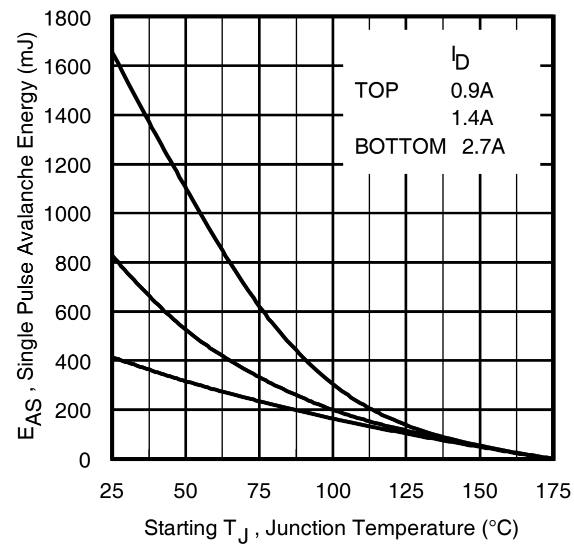


Fig 10. Maximum Avalanche Energy vs. DrainCurrent

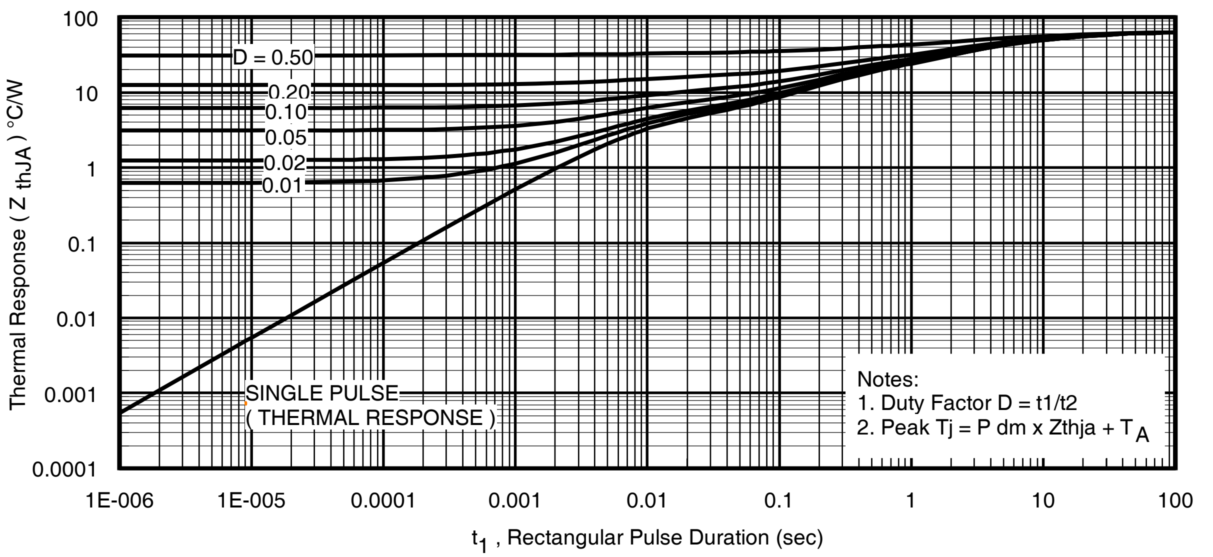
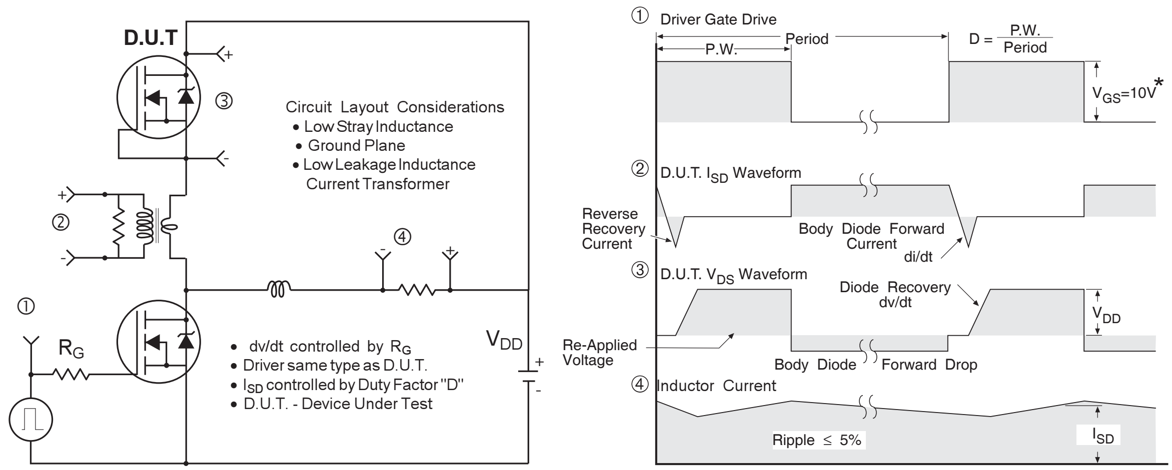


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



* V_{GS} = 5V for Logic Level Devices

Fig 12. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

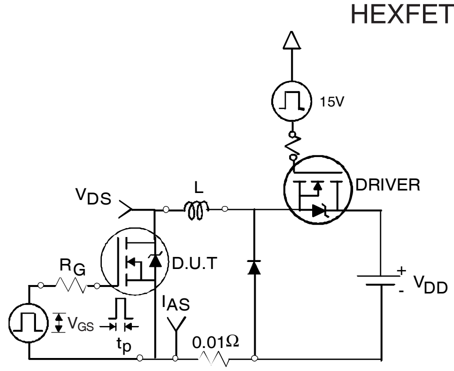


Fig 13a. Unclamped Inductive Test Circuit

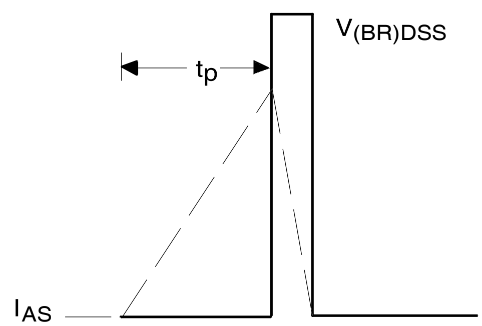


Fig 13b. Unclamped Inductive Waveforms

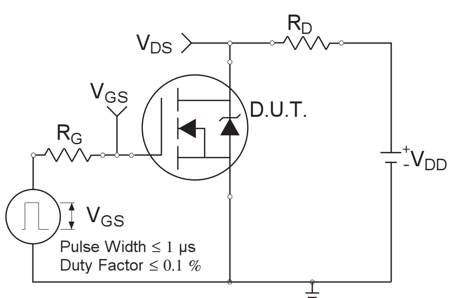


Fig 14a. Switching Time Test Circuit

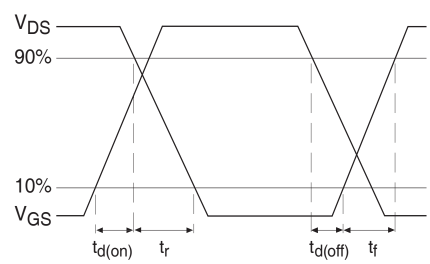


Fig 14b. Switching Time Waveforms

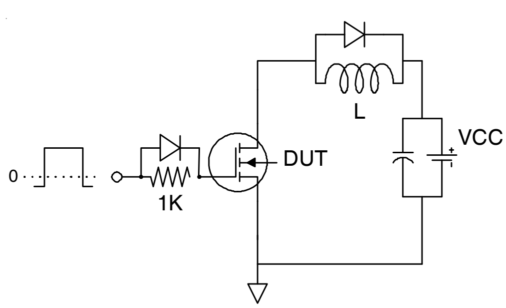


Fig 15a. Gate Charge Test Circuit

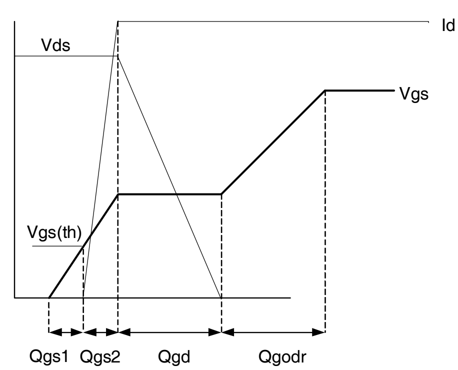
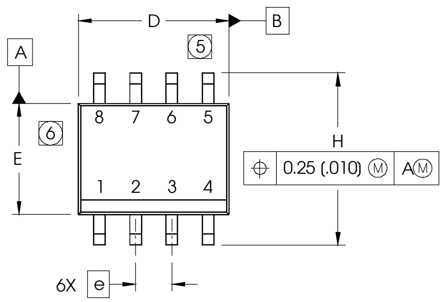


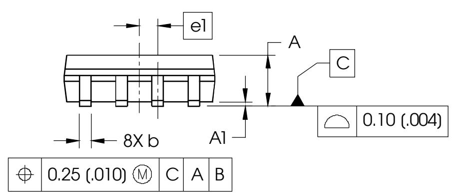
Fig 15b. Gate Charge Waveform

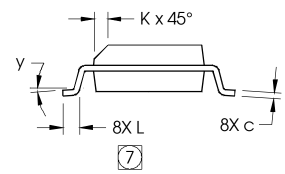
SO-8 Package Outline

Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

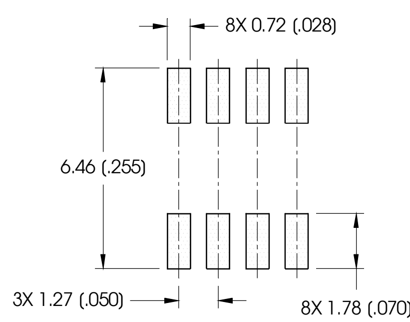




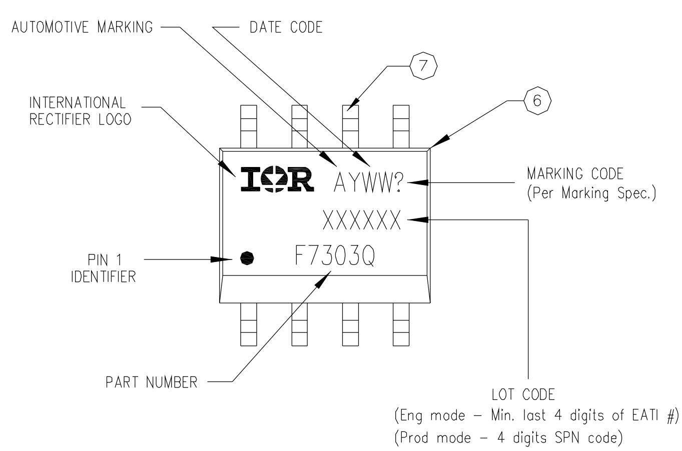
NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



SO-8 Part Marking

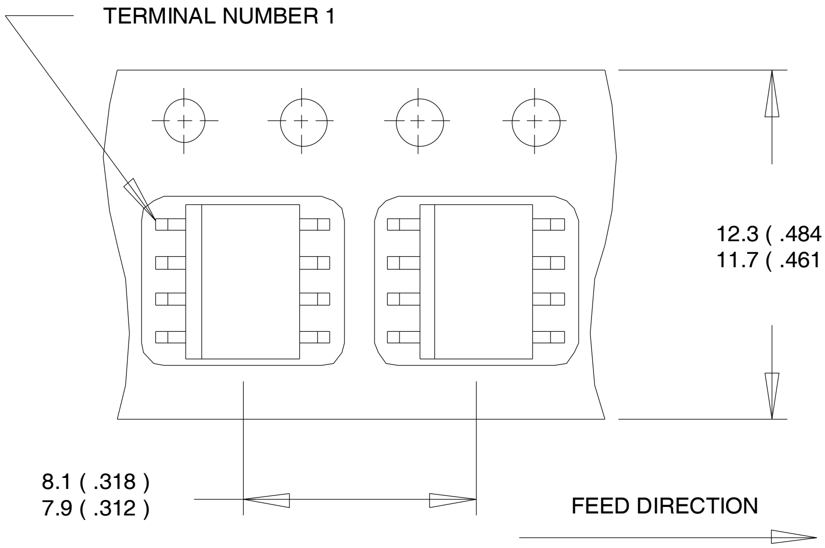


TOP MARKING (LASER)

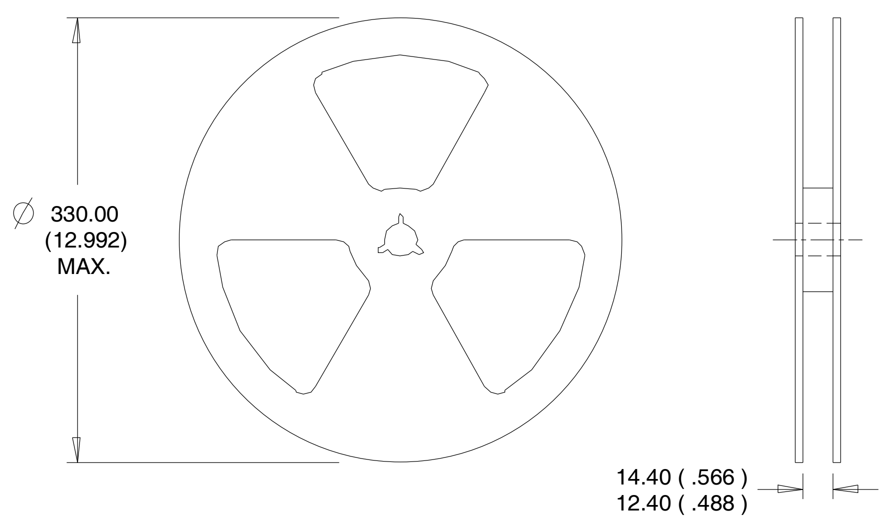
Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Qualification Information†

Qualification Level		Automotive (per AEC-Q101) ††	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		SO-8	MSL1
ESD	Machine Model	Class M2 (+/- 150V)††† AEC-Q101-002	
	Human Body Model	Class H1A (+/- 500V)††† AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 1500V)††† AEC-Q101-005	
RoHS Compliant		Yes	

† Qualification standards can be found at International Rectifier's web site: http//www.irf.com/

†† Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage

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For technical support, please contact IR’s Technical Assistance Center
http://www.irf.com/technical-info/

WORLD HEADQUARTERS:
101 N. Sepulveda Blvd., El Segundo, California 90245
Tel: (310) 252-7105

Revision History

Date	Comments
3/4/2014	• Added "Logic Level Gate Drive" bullet in the features section on page 1 • Updated data sheet with new IR corporate template

AMEYA360
Components Supply Platform

Authorized Distribution Brand :

Website :

Welcome to visit www.ameya360.com

Contact Us :

Address :

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd
Minhang District, Shanghai , China

Sales :

Direct +86 (21) 6401-6692

Email amall@ameya360.com

QQ 800077892

Skype ameyasales1 ameyasales2

Customer Service :

Email service@ameya360.com

Partnership :

Tel +86 (21) 64016692-8333

Email mkt@ameya360.com